

# GL496

## High Speed Infrared Emitting Diode

### ■ Features

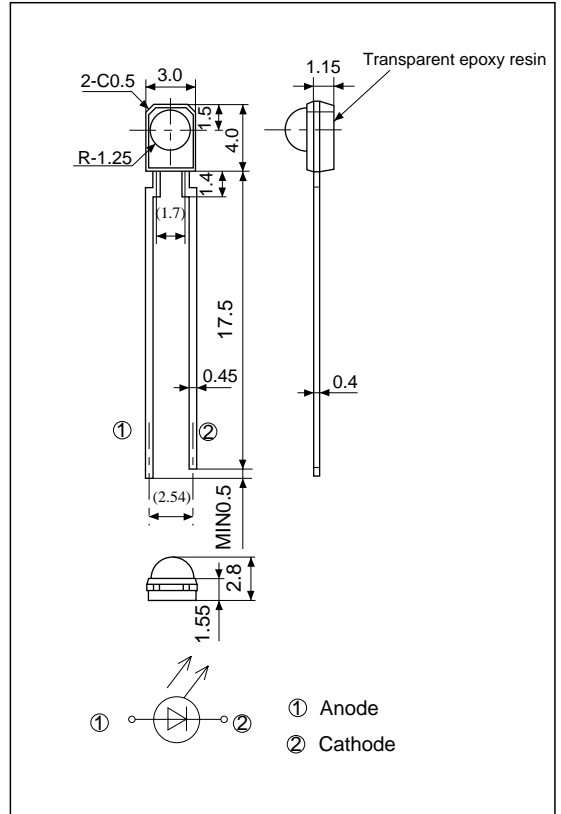
1. High speed response (response frequency : 40MHz)
2. Peak emission wavelength  $\lambda_p$  : TYP. 880 nm
3. Half intensity angle  $\Delta\theta$  :  $\pm 22^\circ$
4. Lead bending type may be used.

### ■ Applications

1. AV equipment
2. Personal computers
3. Portable information terminal equipment

### ■ Outline Dimensions

(Unit : mm)



### ■ Absolute Maximum Ratings

(Ta=25°C)

Parameter	Symbol	Rating	Unit
Forward current	$I_F$	50	mA
*1 Peak forward current	$I_{FM}$	0.5	A
Reverse voltage	$V_R$	4	V
Power dissipation	P	87.5	mW
Operating temperature	$T_{opr}$	- 25 to + 85	°C
Storage temperature	$T_{stg}$	- 40 to + 90	°C
*2 Soldering temperature	$T_{sol}$	260	°C

\*1 Pulse width 100  $\mu$ s, Duty ratio=0.01

\*2 For MAX. 5 seconds at the position of 1.4 mm from the resin edge

**■ Electro-optical Characteristics**

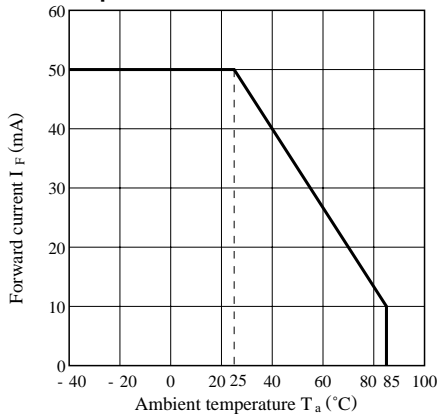
( $T_a=25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Forward voltage	$V_F$	$I_F = 50\text{mA}$	-	1.55	1.75	V
Peak forward voltage	$V_{FM}$	$I_{FM} = 0.5\text{A}$	-	2.6	3.6	V
Reverse current	$I_R$	$V_R = 3\text{V}$	-	-	10	$\mu\text{A}$
<sup>*3</sup> Radiant intensity	$I_E$	$I_F = 50\text{mA}$	3.0	10.0	-	$\text{mW/sr}$
Radiant flux	$\Phi_E$	$I_F = 50\text{mA}$	-	12	-	mW
Peak emission wavelength	$\lambda_p$	$I_F = 50\text{mA}$	850	880	900	nm
Half intensity wavelength	$\Delta \lambda$	$I_F = 50\text{mA}$	-	50	-	nm
Terminal capacitance	$C_t$	$V_R = 0\text{V}, f = 1\text{MHz}$	-	60	-	pF
<sup>*4</sup> Response frequency	$f_c$	$I_F = 50\text{mA} + 10\text{mAp-p}$	-	40	-	MHz
Half intensity angle	$\Delta \theta$	$I_F = 50\text{mA}$	-	$\pm 22$	-	$^\circ$

<sup>\*3</sup> Value obtained by converting the value in power of radiant fluxes emitted at the solid angle of 0.01 sr (steradian) in the direction of mechanical axis of the lens portion into 1 sr or all those emitted from the light emitting diode.

<sup>\*4</sup> Frequency to bring about -3dB reduction of modulated radiant intensity from 100kHz

**Fig. 1 Forward Current vs. Ambient Temperature**



**Fig. 2 Peak Forward Current vs. Duty Ratio**

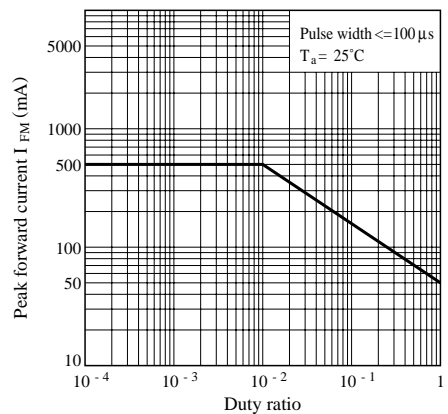


Fig. 3 Spectral Distribution

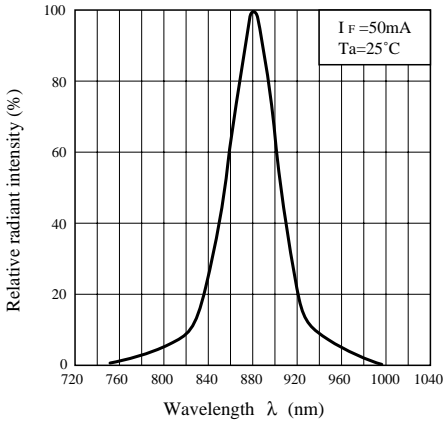


Fig. 4 Peak Emission Wavelength vs. Ambient Temperature

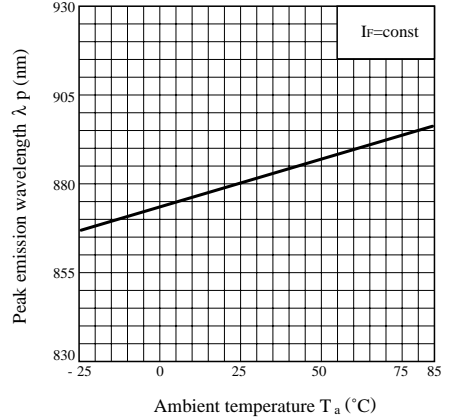


Fig. 5 Forward Current vs. Forward Voltage

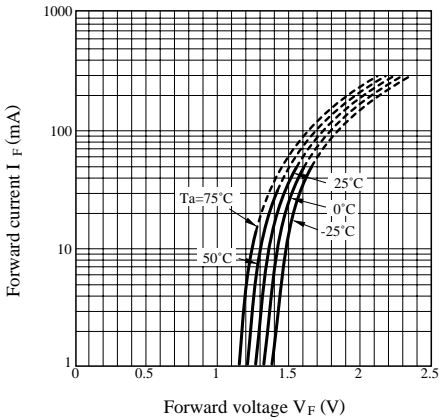


Fig. 6 Relative Radiant Flux vs. Ambient Temperature

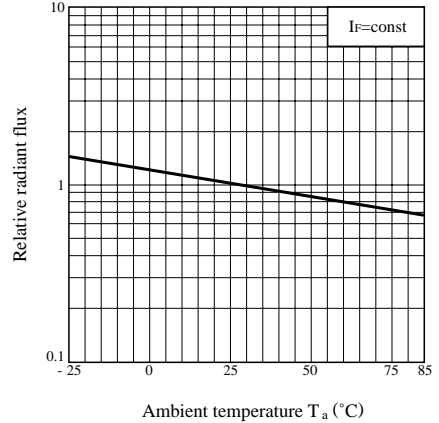


Fig. 7 Radiant Intensity vs. Forward Current

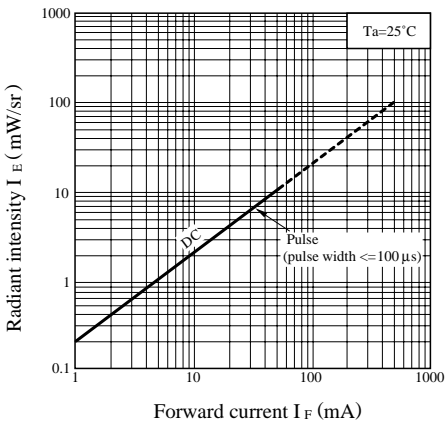


Fig. 8 Relative Radiant Intensity vs. Distance

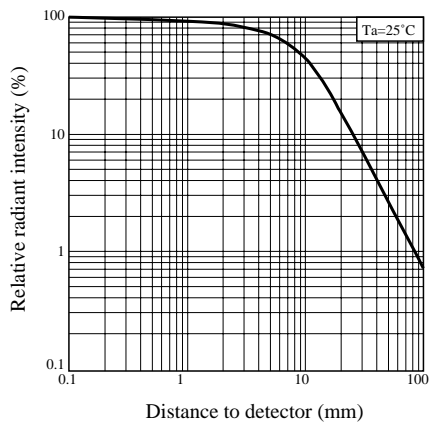


Fig. 9 Relative Radiant Intensity vs. Frequency

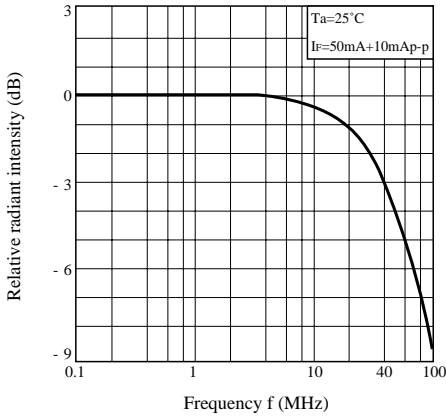


Fig. 10 Relative Collector Current vs. Distance (Detector : PT414PI)

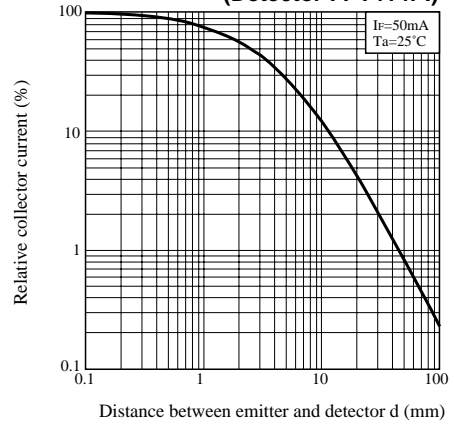
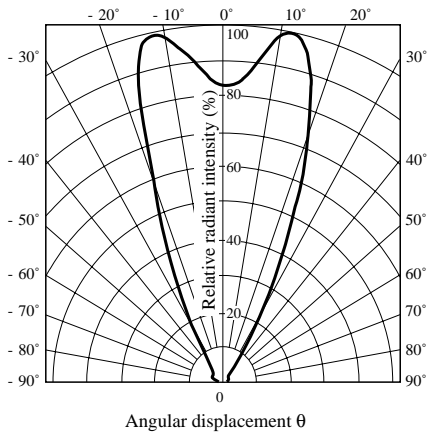


Fig. 11 Radiation Diagram (Ta = 25°C)



● Please refer to the chapter "Precautions for Use". (Page 78 to 93)